



ELECTRONIC TUBE REFERENCE

DF60

Voltage Pentode or Tetrode (under 100V) electronic tube

CONSOLIDATED TECHNICAL DATA

1 SECTION

CONSTRUCTION

PENTODE

Mullard subminiature sharp-cutoff RF pentode for battery-operated equipment, also usable as a frequency changer. Its compact directly heated construction supports both high-frequency amplification and conversion in portable receivers.

GENERAL CHARACTERISTICS

BASE DESIGNATION	—	BASE PINS	8
NOMINAL HEATER	1.25 V / 50 mA	PARALLEL HEATER	— / —
HEATING	Direct	SERIES OPERATION	Not specified
CATHODE ARRANGEMENT	Separate cathodes	SECTION CONSTRUCTION	Similar

SECTION RATINGS

SECTION 1 Pentode	
PLATE RESISTANCE	1000000 Ω
TRANSCONDUCTANCE	0.0011 S
MAXIMUM PLATE VOLTAGE	90 V
MAXIMUM SCREEN VOLTAGE	67.5 V
MAXIMUM CATHODE CURRENT	4 mA
<i>Published Mullard/Philips ratings and characteristics promoted where applicable; additional values retained as parameters.</i>	

The Mullard DF60 is a subminiature sharp-cutoff RF pentode for battery-operated equipment; also usable as a frequency changer.



SOURCE OPERATING CONDITIONS

[SOURCE PDF](#)

1958 Mullard Receiving Tubes

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1958 MULLARD RECEIVING TUBES

Section 1 · Pentode

CHARACTERISTICS

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Cutoff characteristic	Sharp cutoff	—

APPLICATION

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Application	RF amplifier	—



SOURCE OPERATING CONDITIONS

[SOURCE PDF](#)

1963 Mullard

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1963 MULLARD

Section 1 · Pentode

CHARACTERISTICS

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Filament Voltage	1.25 V	DCOnly
Filament Current	50 mA	DCOnly
Plate Voltage	67.5 V	RepresentativeHighVoltagePoint
Screen Voltage	67.5 V	RepresentativeHighVoltagePoint
Plate Current	1.8 mA	RepresentativeHighVoltagePoint
Screen Current	0.48 mA	RepresentativeHighVoltagePoint
Transconductance	1100 μ S	RepresentativeHighVoltagePoint
Plate Resistance	1000000 ohm	RepresentativeHighVoltagePoint

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Input Capacitance	3.7 pF	—
Output Capacitance	4.6 pF	—
Plate-Grid Capacitance	0.01 pF	Maximum

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
Conversion Transconductance	320 uS	FrequencyChanger; Va=67.5V
Maximum Plate Voltage	90 V	—
Maximum Screen Voltage	67.5 V	—
Maximum Cathode Current	4 mA	—